

1018

ISSUE CLASSIFICATION	
Class	Section

PATENT NUMBER 11

U.S. **UTILITY** Patent Application

<p>O.I.P.E.</p> <p>SCANNED <u>MI</u> Q.A. <u>Do 1</u></p>	<p>PATENT DATE</p>
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APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER
09/981848	F	117		1765	JOE RSON

APPLICANTS

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TITLE

Crystal growth method, crystal growth apparatus, group-III nitride crystal and group-III nitride semiconductor device

PTO-2040
12/89

ISSUING CLASSIFICATION												
ORIGINAL				CROSS REFERENCE(S)								
CLASS		SUBCLASS		CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)							
INTERNATIONAL CLASSIFICATION												

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<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
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